

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-6. (Canceled)

7. (Withdrawn-Currently Amended) An SOI wafer in which a base wafer and a bond wafer respectively consisting of silicon single crystal are bonded via an oxide film having a thickness of 10 nm - 100 nm, and then the bond wafer is thinned to form a silicon active layer, wherein the base wafer is formed of silicon single crystal grown by Czochralski method, and ~~the a~~ whole surface of the base wafer is ~~within~~ within an N region outside ~~OSF~~ of an OSF region and ~~doesn't~~ does not include a defect region detected by Cu deposition method, or the whole surface of the base wafer is within a region outside of the OSF region, ~~doesn't~~ does not include a defect region detected by Cu deposition method, and includes ~~I~~ an I region containing dislocation cluster due to interstitial silicon.

8. (Withdrawn) The SOI wafer according to Claim 7, wherein the SOI wafer is produced by ion implantation delamination method in which ions are implanted into the bond wafer and the bond wafer is thinned by delamination at the ion-implanted layer.

9-10. (Canceled)

11. (Withdrawn-Currently Amended) The SOI wafer according to claim 7, wherein the silicon active layer consists of silicon single crystal grown by Czochralski method, and the whole surface of the silicon active layer is within the N region outside of the OSF region and ~~doesn't~~ does not include ~~defect~~ the defect region detected by Cu deposition method.

12. (Withdrawn-Currently Amended) The SOI wafer according to claim 8, wherein the silicon active layer consists of silicon single crystal grown by Czochralski

method, and the whole surface of the silicon active layer is within the N region outside of the OSF region and ~~doesn't~~ does not include the defect region detected by Cu deposition method.

13-14. (Canceled)

15. (Currently Amended) A method for producing an SOI wafer comprising at least the ~~steps of;~~ steps of: forming an oxide film having a thickness of 10 nm - 100 nm, an oxide film at least on one of a base wafer and a bond wafer respectively consisting of silicon single crystal, implanting ions into the bond wafer to form an ion-implanted layer, bonding ~~the surface~~ a surface of the ion-implanted an ion-implanted side of the bond wafer and the base wafer via the oxide film, and delaminating the bond wafer at the ion-implanted layer as a boundary, wherein the base wafer ~~is used, which is~~ formed of silicon single crystal grown by Czochralski method, and the whole surface of the base wafer is within ~~N region~~ N region formed at lower speed ~~than~~ than an OSF region generated in a ring shape when grown with gradually decreasing pulling rate from high speed to low speed, and ~~doesn't~~ does not include ~~defect~~ a defect region detected by Cu deposition method, or the whole surface of the base wafer is within a region formed at lower speed than the OSF region generated in a ring shape when grown with gradually decreasing pulling rate from high speed to low speed, ~~doesn't~~ does not include ~~defect~~ the defect region detected by Cu deposition method, and includes ~~I region~~ I region containing dislocation cluster due to interstitial silicon.

16. (Currently Amended) The method for producing an SOI wafer according to claim 15, wherein the bond wafer is ~~used, which is~~ formed of silicon single crystal grown by Czochralski method, and of which the whole surface is within the N region formed at lower speed than the OSF region generated in a ring shape when grown with gradually decreasing pulling rate from high speed to low speed and ~~doesn't~~ does not include the defect region detected by Cu deposition method.